

# EPIGAP Optronik GmbH

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## Data Sheet

### LED Chip blue

### EOLC-430-34

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Radiation	Type	Electrodes
blue	GaN / sapphire	P + N up

<p style="text-align: center;">Unit: µm</p>	<p>Description</p> <ul style="list-style-type: none"> <li>- Substrate: sapphire, epitaxial layer: GaN based material</li> <li>- N bonding pad electrode: Au alloy</li> <li>- P bonding pad electrode: Au alloy</li> </ul> <p style="font-size: small;">Above drawing is not on real scale</p>
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### Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		$I_F$			20	mA
Peak forward current	$t_p \leq 50 \mu\text{s}$ , $t_p/T = 1/2$	$I_{FM}$			100	mA

### Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	$V_F$		3.5	3.8	V
Reverse current	$V_R = 5 \text{ V}$	$I_R$			1	$\mu\text{A}$
Radiant power*	$I_F = 20 \text{ mA}$	$\Phi_e$		16		mW
Radiant intensity*	$I_F = 20 \text{ mA}$	$I_e$		3.35		mW/sr
Luminous flux*	$I_F = 20 \text{ mA}$	$\Phi_v$		0.12		lm
Luminous intensity*	$I_F = 20 \text{ mA}$	$I_v$		32		mcd
Peak wavelength	$I_F = 20 \text{ mA}$	$\lambda_p$	425	428	430	nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		15	30	nm

\*Measured on bare chip on TO-18 header

### Packing

Chips on adhesive film with wire-bond side top

Art. No. 112 013



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.